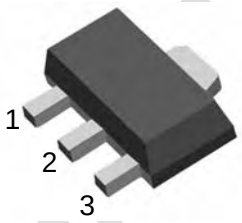
KTA1664 TRANSISTOR (PNP)

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

Power dissipation

$P_{CM:}$ 0.5 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.8 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-1mA, I_E=0	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-10mA, I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	100		320	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-700mA	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-20mA			-0.7	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA	-0.5		-0.8	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		19		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320
Marking	**RO**	**RY**